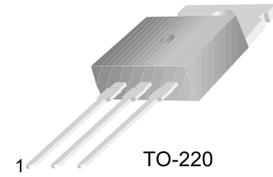


TIP41 Series(TIP41/41A/41B/41C)

Medium Power Linear Switching Applications

- Complement to TIP42/42A/42B/42C



TO-220
1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Emitter Voltage: TIP41	40	V
	: TIP41A	60	V
	: TIP41B	80	V
	: TIP41C	100	V
V_{CEO}	Collector-Emitter Voltage: TIP41	40	V
	: TIP41A	60	V
	: TIP41B	80	V
	: TIP41C	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	6	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	2	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	65	W
P_C	Collector Dissipation ($T_a=25^\circ\text{C}$)	2	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage	$I_C = 30\text{mA}, I_B = 0$	40		V
	: TIP41				
	: TIP41A				
	: TIP41B				
I_{CEO}	Collector Cut-off Current	$V_{CE} = 30\text{V}, I_B = 0$ $V_{CE} = 60\text{V}, I_B = 0$		0.7	mA
	: TIP41/41A : TIP41B/41C				
I_{CES}	Collector Cut-off Current	$V_{CE} = 40\text{V}, V_{EB} = 0$ $V_{CE} = 60\text{V}, V_{EB} = 0$ $V_{CE} = 80\text{V}, V_{EB} = 0$ $V_{CE} = 100\text{V}, V_{EB} = 0$		400	μA
	: TIP41				
	: TIP41A				
	: TIP41B : TIP41C				
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$		1	mA
h_{FE}	* DC Current Gain	$V_{CE} = 4\text{V}, I_C = 0.3\text{A}$ $V_{CE} = 4\text{V}, I_C = 3\text{A}$	30	75	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = 6\text{A}, I_B = 600\text{mA}$		1.5	V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$V_{CE} = 4\text{V}, I_C = 6\text{A}$		2.0	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	3.0		MHz

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycles $\leq 2\%$